



DMN6075S

### **60V N-CHANNEL ENHANCEMENT MODE MOSFET**

### Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
60V	85mΩ @ V <sub>GS</sub> = 10V	2.5A
000	120mΩ @ $V_{GS}$ = 4.5V	2.0A

### Description

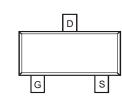
This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# Applications

- DC-DC Converters
- Power Management Functions
- Backlighting



Top View



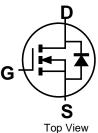
Top View

# **Features and Benefits**

- N MOSFET
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208 3
- Weight: 0.008 grams (Approximate)



Top View Pin Configuration

### Ordering Information (Note 4)

Product	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DMN6075S-7	7	8	3,000
DMN6075S-13	13	8	10,000

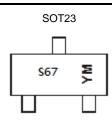
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

 See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



S67 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: E = 2017) M = Month (ex: 9 = September)

#### Date Code Key

Duie Coue	КОУ												
Year	2014		~	2017	2018	2019	2020	202	1 20	22	2023	2024	2025
Code	В		~	E	F	G	Н			J	K	L	М
Mont	h	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	)	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	60	V		
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5) $V_{GS}$ = 10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	2.0 1.5	A
$ \begin{array}{c c} \mbox{Continuous Drain Current (Note 6) } V_{GS} = 10V & \begin{array}{c} \mbox{Steady} & T_A = +25^{\circ}C \\ \mbox{State} & T_A = +70^{\circ}C \end{array} \end{array} $		ID	2.5 2.0	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	12	А

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C		0.8	W	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +70°C	PD	0.5		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ ext{ heta}JA}$	157	°C/W	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	D	1.15	W	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +70°C	PD	0.7	vv	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	110	°C/W	
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

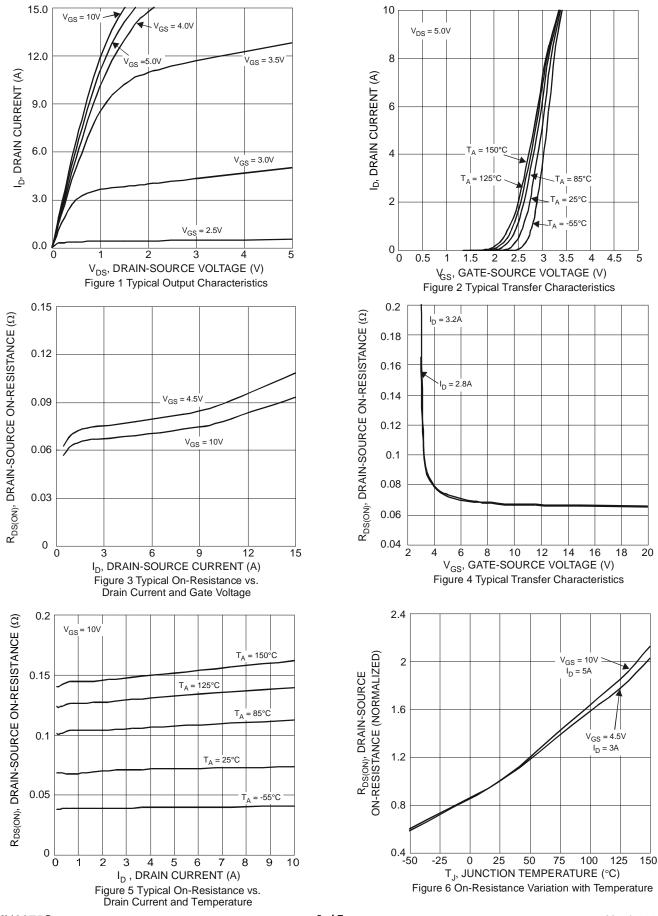
Characteristic	Cumph of	Min	Turn	May	11	Test Canditian
	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)		[	1	1	1	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	—	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	_		1.0	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	Igss	—	—	±100	nA	$V_{GS} = \pm 16V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	_	3	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$
	_		69	85		V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.2A
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	75	120	mΩ	$V_{GS} = 4.5V, I_D = 2.8A$
Diode Forward Voltage	V <sub>SD</sub>	_		1.2	V	$V_{GS} = 0V, I_{S} = 2.5A$
DYNAMIC CHARACTERISTICS (Note 8)			•	•	•	
Input Capacitance	Ciss	_	606	—	pF	
Output Capacitance	Coss	_	32.6	_	pF	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	24.6	_	pF	
Gate Resistance	Rg	_	1.5	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	12.3	—	nC	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	5.6	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	_	1.7	—	nC	$V_{DS} = 30V, I_D = 3A$
Gate-Drain Charge	Q <sub>gd</sub>	_	1.9	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>		3.5	_	ns	
Turn-On Rise Time	t <sub>R</sub>		4.1	_	ns	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 30V,
Turn-Off Delay Time	t <sub>D(OFF)</sub>		35	_	ns	$R_g = 20\Omega, R_L = 50\Omega$
Turn-Off Fall Time	t <sub>F</sub>	_	11	—	ns	1

Notes:

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

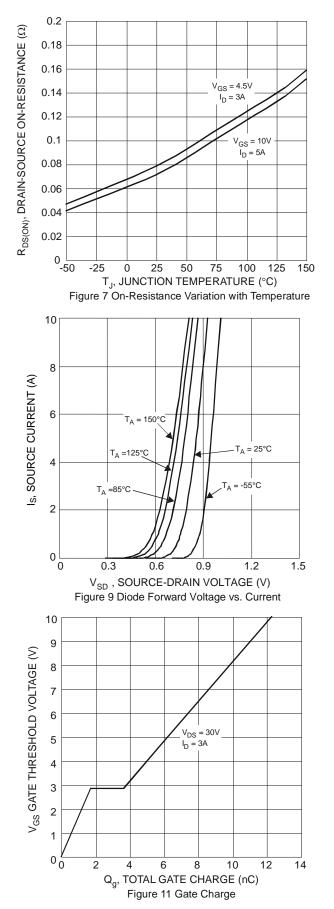


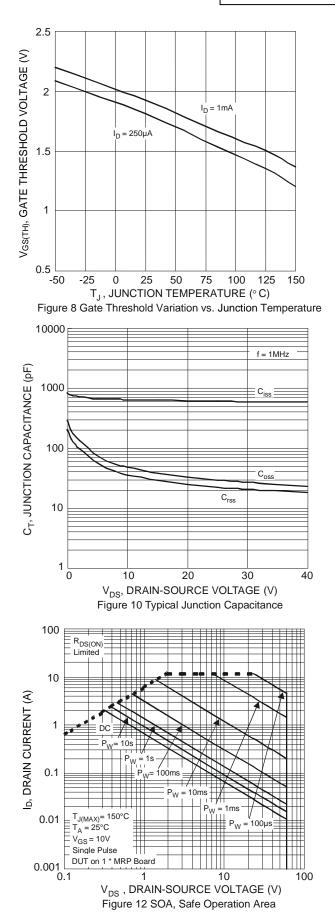


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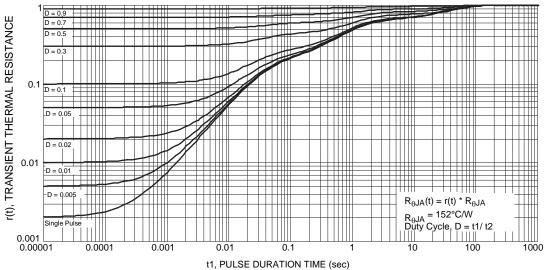
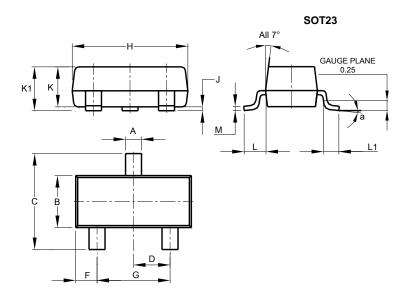


Figure 13 Transient Thermal Resistance



# **Package Outline Dimensions**

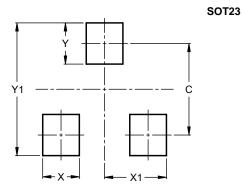
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
H	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All	Dimens	ions in	mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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